

**2N3585**

**5 Amp, 500V,  
 High Voltage  
 NPN Silicon Power  
 Transistors**

**APPLICATIONS:**

- Off-Line Inverters
- Switching Regulators
- Motor Controls
- Deflection Circuits
- DC-DC Converters
- High Voltage Amplifiers

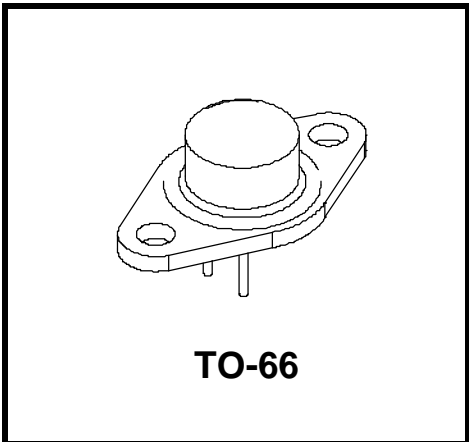
**FEATURES:**

- High Voltage: 250 to 500V
- Fast Switching:  $t_f < 3\mu\text{sec.}$
- High Power: 35 Watts
- High Current: 2 Amps
- Low  $V_{CE(SAT)}$

**DESCRIPTION:**

These power transistors are produced by PPC's DOUBLE DIFFUSED PLANAR process. This technology produces high voltage devices with excellent switching speeds, frequency response, gain linearity, saturation voltages, high current gain, and safe operating areas. They are intended for use in Commercial, Industrial, and Military power switching, amplifier, and regulator applications.

Ultrasonically bonded leads and controlled die mount techniques are utilized to further increase the SOA capability and inherent reliability of these devices. The temperature range to 200°C permits reliable operation in high ambients, and the hermetically sealed package insures maximum reliability and long life.



**ABSOLUTE MAXIMUM RATINGS:**

SYMBOL	CHARACTERISTIC	VALUE	UNITS
$V_{CBO}^*$	Collector-Base Voltage	500	Volts
$V_{CEO}^*$	Collector-Emitter Voltage	300	Volts
$V_{CER}^*$	Collector-Emitter Voltage $R_{BE} = 50\Omega$	400	Volts
$V_{EBO}^*$	Emitter-Base Voltage	6	Volts
$I_C^*$	Peak Collector Current	5	Amps
$I_C^*$	Continuous Collector Current	2	Amps
$I_B^*$	Base Current	1	Amps
$T_{STG}^*$	Storage Temperature	-65 to 200	°C
$T_J^*$	Operating Junction Temperature	-65 to 200	°C
*	Lead Temperature 1/16" from Case for 10 Sec.	235	°C
$P_T^*$	Power Dissipation	35	Watts
$\theta_{JC}$	$T_C = 25^\circ\text{C}$ Thermal Impedance	5.0	°C/W

\* Indicates JEDEC registered data.

**ELECTRICAL CHARACTERISTICS:  
 (25° Case Temperature Unless Otherwise Noted)**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE		Units
			Min.	Max.	
$V_{CE(sus)}^*$	Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ Amp}$ (Notes 1 and 2)	300	----	Volts
$V_{CER(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 0.2A, R_{BE} = 50\Omega$ (Notes 1 and 2)	400	----	Volts
$I_{CEV}^*$	Collector Cutoff Current	$V_{CE} = 450V, V_{BE} = -1.5V$	----	1.0	mA.
$I_{CEV}^*$	Collector Cutoff Current $T_C = 150^\circ C$	$V_{CE} = 300V, V_{BE} = -1.5V$	----	3.0	mA.
$I_{CEO}^*$	Collector Cutoff Current	$V_{CE} = 150V, I_B = 0$	----	5.0	mA.
$I_{EB0}^*$	Emitter Cutoff Current	$V_{EB} = 6V, I_C = 0$	----	0.5	mA.
$h_{FE}^*$	DC Forward Current Transfer Ratio (Note 1)	$I_C = 0.1A, V_{CE} = 10V$ $I_C = 1.0A, V_{CE} = 10V$ $I_C = 1.0A, V_{CE} = 2V$	40 25 8	---- 100 80	---- ---- ----
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage (Note 1)	$I_C = 1.0A, I_B = 0.125A$	----	0.75	Volts
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage (Note 1)	$I_C = 1.0A, I_B = 0.10A$	----	1.4	Volts
$I_{S/b}$	Second-Breakdown Collector Current (with base forward biased)	$V_{CE} = 100V, t = 1.0sec.$	0.35	----	A
$E_{S/b}^*$	Second-Breakdown Energy (with base reverse biased)	$V_{EB} = 4V, R_{BE} = 20\Omega, L = 100\mu h$	200	----	$\mu J$
$h_{fe}^*$	Common-Emitter Small-Signal Forward Current Transfer Ratio	$V_{CE} = 10V, I_C = 0.2A, f = 5 \text{ MHz}$	3	----	----
$ h_{fe} ^*$	Common-Emitter Small-Signal Forward Current Transfer Ratio, $f = 5 \text{ MHz}$	$V_{CE} = 10V, I_C = 0.2A$	2.0	----	----
$C_{Ob}$	Collector-Base Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$	----	120	pf
$tr^*$	Rise Time	$I_C = 1.0A, I_{B2} = 0.10A$	----	3.0	$\mu sec.$
$ts^*$	Storage Time	$I_C = 1.0A, I_{B1} = I_{B2} = 0.10A$	----	4.0	$\mu sec.$
$tf^*$	Fall Time	$I_C = 1.0A, I_{B1} = I_{B2} = 0.10A$	----	3.0	$\mu sec.$

Note 1: Pulse Test: Pulse width = 300 $\mu$ Sec., Rep. Rate 60Hz.

Note 2: Caution - Do not use Curve Tracer.

\* Indicates JEDEC registered data.

**PACKAGE MECHANICAL DATA:**

